

# Spin-sensitive Bleaching and Spin-Relaxation in QW's

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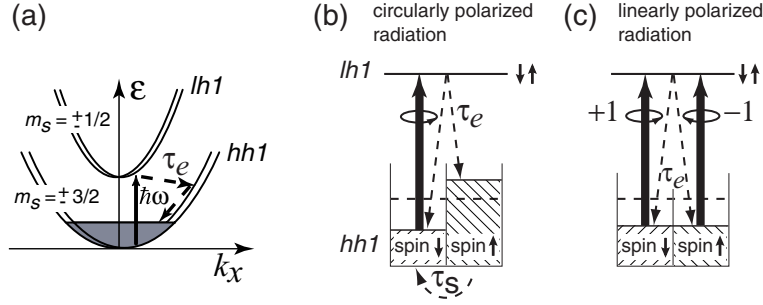
Spin-sensitive saturation of absorption of infrared radiation has been investigated in *p*-type GaAs QWs. It is shown that the absorption saturation of circularly polarized radiation is mostly controlled by the spin relaxation time of the holes. The saturation behavior has been investigated for different QW widths and in dependence on the temperature with the result that the saturation intensity substantially decreases with narrowing of QWs. Spin relaxation times were experimentally obtained by making use of calculated (linear) absorption coefficients for inter-subband transitions.

**1 Introduction** The investigation of spin relaxation has attracted considerable attention in the past because of its great importance for the development of active spintronic devices [1]. Current investigations of the spin lifetime in semiconductor devices are based on optical spin orientation by inter-band excitation and further tracing the kinetics of polarized photoluminescence. These studies give important insights into the mechanisms of spin relaxation of photoexcited free carriers. Recently, the spin-sensitive bleaching of infrared absorption has been observed in *p*-type QWs yielding an access to spin relaxation processes under the condition of monopolar spin orientation [2]. In contrast to conventional methods of optical spin orientation using inter-band transitions [3] to create electron-hole pairs, in the infrared due to inter-subband transitions only one type of charge carriers is excited. Here we show that infrared spin orientation allows to study spin relaxation without electron-hole interaction and exciton formation.

**2 Experiment** The experiments have been carried out on *p*-type (113) MBE-grown GaAs QWs with various well widths  $L_W$  between 7 and 20 nm and on (001)-miscut QWs grown by MOCVD with a width of 20 nm. Samples with free carrier densities  $p_s$  of about  $2 \cdot 10^{11} \text{ cm}^{-2}$  and a very high mobility  $\mu$  of around  $5 \cdot 10^5 \text{ cm}^2/(\text{Vs})$  (at 4.2 K) were studied in the range of 4.2 K up to 120 K. As radiation source a high power far-infrared (FIR) molecular laser, optically pumped by a TEA-CO<sub>2</sub> laser, has been used delivering 100 ns pulses with intensities up to  $1 \text{ MW/cm}^2$  at a wavelength range between 35  $\mu\text{m}$  and 148  $\mu\text{m}$ .

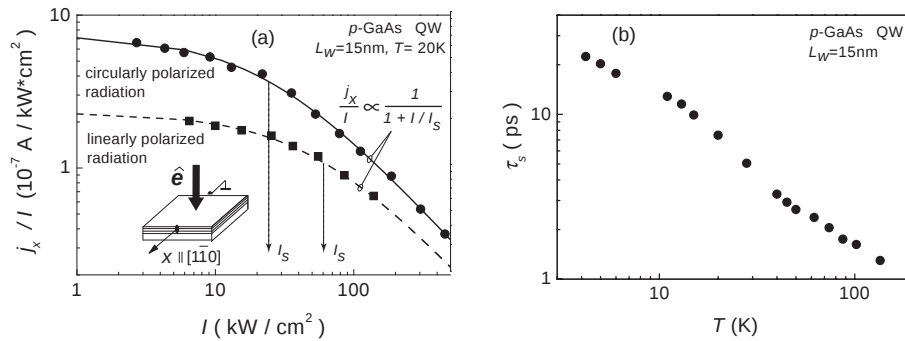
The intensity dependence of the absorption coefficient has been investigated showing that absorption saturates with higher intensities. It is observed that for circularly polarized radiation, compared to linearly polarized radiation, saturation takes place at a lower level of intensity. The basic physics of spin sensitive bleaching of absorption is sketched in Fig. 1. Excitation with FIR radiation results in direct transitions between heavy-hole  $hh1$  and light-hole  $lh1$  subbands. This process depopulates and populates selectively

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**Fig. 1** Microscopic picture of spin-sensitive bleaching: (a)- direct  $hh1$ - $lh1$  optical transitions. (b) and (c)- process of bleaching for circular and linear polarized radiation, respectively. Dashed arrows indicate energy ( $\tau_e$ ) and spin ( $\tau_s$ ) relaxation.

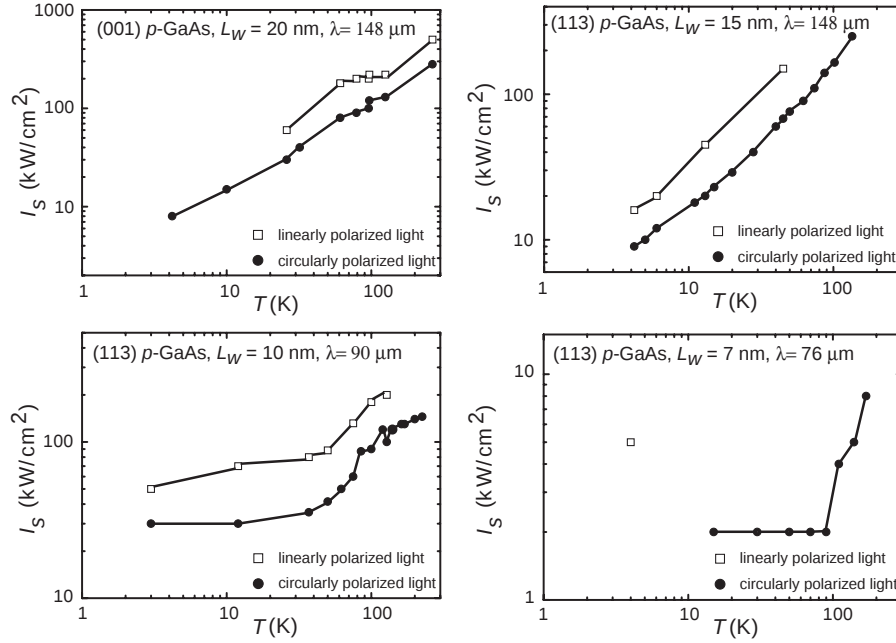
spin states in  $hh1$  and  $lh1$  subbands. The absorption is proportional to the difference of populations of the initial and final states. At high intensities the absorption decreases since the photoexcitation rate becomes comparable to the non-radiative relaxation rate to the initial state. Due to selection rules only one type of spins is involved in the absorption of circularly polarized light. Thus the absorption bleaching of circularly polarized radiation is governed by energy relaxation of photoexcited carriers and spin relaxation in the initial subband (see Figs. 1a and 1b). These processes are characterized by energy and spin relaxation times  $\tau_e$  and  $\tau_s$ , respectively. We note, that during energy relaxation to the initial state in  $hh1$  the holes lose their photoinduced orientation due to rapid relaxation [4]. Thus, spin orientation occurs in the initial subband  $hh1$ , only. In contrast to circularly polarized light, absorption of linearly polarized light is not spin selective and the saturation is controlled by the energy relaxation only (see Fig. 1c). If  $\tau_s$  is longer than  $\tau_e$ , bleaching of absorption becomes spin sensitive and the saturation intensity  $I_s$  of circularly polarized radiation drops below the value of linear polarization (see Fig. 2a).



**Fig. 2** a) CPGE and LPGE currents  $j_x$  normalized by intensity  $I$  as a function of  $I$  for circularly and linearly polarized radiation of  $\lambda = 148 \mu\text{m}$ , respectively [2]. (b) Spin relaxation times obtained for  $p$ -type GaAs sample with a QW of  $L_W = 15 \text{ nm}$  width,  $p_s = 1.66 \cdot 10^{11} \text{ cm}^{-2}$  and  $\mu$  of about  $5 \cdot 10^5 \text{ cm}^2/(\text{Vs})$ .

The difference in absorption bleaching for circularly and linearly polarized radiation has been observed experimentally [2] employing the spin orientation induced circular photogalvanic effect (CPGE) [5] and the linear photogalvanic effect (LPGE) [6]. The absorption coefficient is proportional to the photogalvanic current  $j_x$  normalized by the radiation intensity  $I$ . Fig. 2a shows that the photocurrent  $j_x$  measured on  $p$ -type GaAs QWs depends on intensity  $I$  as  $j_x \propto I/(1 + I/I_s)$ , where  $I_s$  is the saturation intensity. For different temperatures and QW widths our experiments show that saturation intensities  $I_s$  for circularly polarized radiation are generally smaller than for linearly polarized radiation (Fig. 3).

The non-linear behavior of the photogalvanic current has been analyzed in terms of excitation-relaxation kinetics taking into account both optical excitation and non-radiative relaxation processes. It can be



**Fig. 3** Temperature dependence of the saturation intensities for various QW widths for linear (squares) and circular (circles) polarized light, respectively. The thickness of the QWs decreases from top left to bottom right. Note that the sample top left is miscut (001) grown.

shown [2] that the photocurrent  $j_{LPGE}$  induced by linearly polarized radiation is described by  $j_{LPGE}/I \propto (1 + I/I_{se})^{-1}$ , where  $I_{se}$  is the saturation intensity controlled by energy relaxation of the hole gas. The photocurrent  $j_{CPGE}$  induced by circularly polarized radiation is proportional to  $I / (1 + I(I_{se}^{-1} + I_{ss}^{-1}))$  where  $I_{ss} = \hbar\omega p_s / (\alpha_0 L_W \tau_s)$  is the saturation intensity controlled by hole spin relaxation. Here  $\alpha_0$  is the absorption coefficient at low intensities and the spin relaxation time  $\tau_s$  can be evaluated as

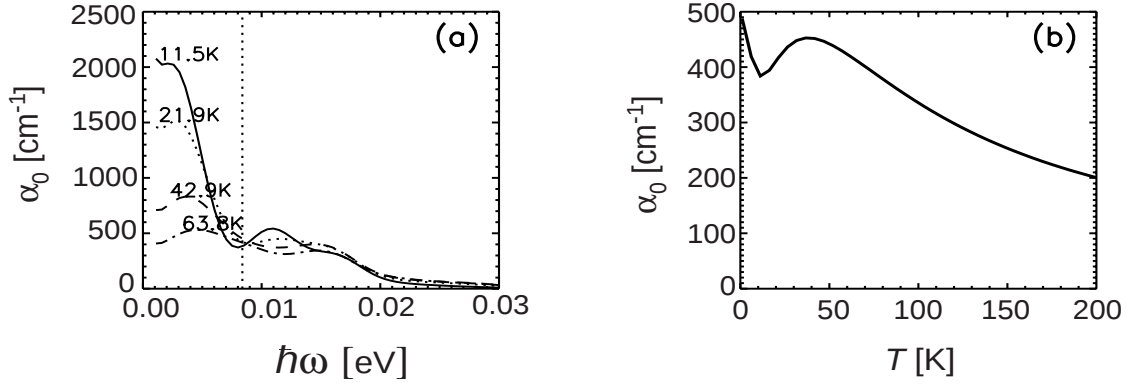
$$\tau_s = \frac{\hbar\omega p_s}{\alpha_0 L_W I_{ss}} \quad (1)$$

Using experimentally obtained  $I_{ss}$  together with  $\alpha_0$ , spin relaxation times  $\tau_s$  can be derived. The absorption coefficient is determined theoretically.

The calculations of the linear absorption coefficient  $\alpha_0$  for inter-subband transitions are based on the self-consistent multi-band envelope function approximation (EFA) [7], that takes into account the crystallographic orientation of the QW (here the (113) direction) and the doping profile. Calculations are performed here within the Luttinger model of the heavy and light hole states to obtain the hole subband dispersion  $\epsilon_i(\mathbf{k})$  and eigenstates  $|i, \mathbf{k}\rangle$  of the hole subband  $i$  and in-plane wave-vector  $\mathbf{k}$ . For direct (electric dipole) transitions between subbands  $i$  and  $j$  the contribution to the absorption coefficient  $\alpha_{i \rightarrow j}(\omega)$  as a function of the excitation energy  $\hbar\omega$  is then given by [8]

$$\alpha_{i \rightarrow j}(\omega) = \frac{e^2}{4\pi\epsilon_0\omega cn L_W} \int d^2k |\langle j, \mathbf{k} | \mathbf{e} \cdot \hat{\mathbf{v}}(\mathbf{k}) | i, \mathbf{k} \rangle|^2 [f_j(\mathbf{k}) - f_i(\mathbf{k})] \frac{e^{-(\epsilon_j(\mathbf{k}) - \epsilon_i(\mathbf{k}) - \hbar\omega)^2 / \Gamma^2}}{\sqrt{\pi}\Gamma}, \quad (2)$$

where  $\mathbf{e}$  is the light polarization vector,  $n$  is the refractive index,  $\epsilon_0$  is the free-space permittivity,  $f_i(\mathbf{k})$  is the Fermi distribution function in the subband  $i$  and  $\Gamma$  is a broadening parameter to account for the level broadening due to scattering. Within EFA, the velocity  $\hat{\mathbf{v}}(\mathbf{k})$  is a matrix operator expressed as the gradient in  $\mathbf{k}$ -space of the Luttinger Hamiltonian. Its matrix elements are calculated from the EFA wave functions.



**Fig. 4** (a) Absorption coefficient as a function of photon energy  $\hbar\omega$  for various temperatures and (b) as a function of  $T$  for  $\hbar\omega = 8.4 \text{ meV}$  (vertical dotted line in (a)). The parameters of the calculation were chosen for a (113)-grown 15 nm GaAs-AlGaAs QW with carrier density  $2 \cdot 10^{11} \text{ cm}^{-2}$  and the broadening  $\Gamma$  was set to 2.47 meV.

Following this scheme we calculate the absorption coefficient  $\alpha_0(\omega) = \sum_{ij} \alpha_{i \rightarrow j}(\omega)$ . The absorption spectrum for the system with  $L_W = 15 \text{ nm}$  is shown in Fig. 4a. At low temperatures two pronounced peaks evolve, which correspond to the transitions from the lowest (spin split) hole subband to the second and third subband, respectively. Fig. 4b shows the temperature dependence (due to the Fermi distribution function) of  $\alpha_0$  at the excitation energy for the sample with  $L_W = 15 \text{ nm}$ . Using experimentally obtained  $I_{ss}$  together with the calculated values of  $\alpha_0$ , spin relaxation times can be obtained [2]. The results are given in Fig. 2. Compared to the values given in [2], where  $\alpha_0$  was derived from [8], here we obtain smaller  $\tau_s$  at high temperatures due to a more realistic theoretical model for the calculation of  $\alpha_0$ . We note that in the definition of  $I_{ss}$  it was assumed that the spin selection rules are fully satisfied at the transition energy. This is the case for optical transitions occurring close to  $k = 0$  in (001)-grown systems [4]. However, in (113)-grown systems, heavy-hole and light-hole subbands show a strong mixture, which exists even at  $k = 0$ . This reduces the strength of the selection rules [9] and therefore the efficiency of spin orientation. The mixing can be taken into account by means of a multiplicative factor in  $I_{ss}$ , which increases the saturation intensity at constant spin relaxation time.

The results of Fig. 3 for QWs of various widths show a significant reduction of  $I_{ss}$  with decreasing  $L_W$ . This observation indicates longer hole spin relaxation times for narrower QW in accordance with calculations by Ferreira and Bastard [4]. A verification of this tendency requires the extraction of spin relaxation times – which has been done here only for  $L_W = 15 \text{ nm}$  (Fig. 2b) – also for the other samples.

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